

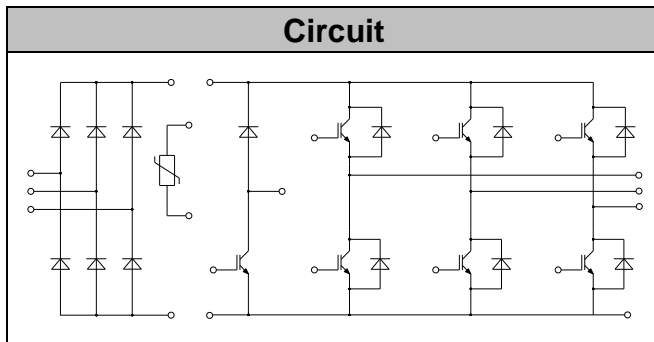


## IGBT Modules

$V_{CES}$	1200V
$I_c$	100A

## Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)



## Features

- Low switching losses
- Low  $V_{CE(sat)}$  with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C

## ● IGBT- inverter

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_c=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_c$	$T_c=100^{\circ}C, T_{vjmax}=175^{\circ}C$	100	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	200	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_c=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	515	W



## ● IGBT- inverter

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=3.3mA, T_{vj}=25^{\circ}C$	5.0	5.8	6.5	V	
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.85	2.50	V	
		$I_C=100A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.15			
		$I_C=100A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.25			
Gate Charge	$Q_G$			0.78		uC	
Internal Gate Resistance	$R_{gint}$			7.5		$\Omega$	
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		6.8		nF	
Reverse Transfer Capacitance	$C_{res}$			0.32		nF	
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=5.6\Omega$ $T_{vj}=25^{\circ}C$		160		ns	
Rise Time	$t_r$			45		ns	
Turn-off Delay Time	$t_{d(off)}$			215		ns	
Fall Time	$t_f$			54		ns	
Energy Dissipation During Turn-on Time	$E_{on}$			9.2		mJ	
Energy Dissipation During Turn-off Time	$E_{off}$			5.8		mJ	
Turn-on Delay Time	$t_{d(on)}$		$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=5.6\Omega$ $T_{vj}=150^{\circ}C$		198		ns
Rise Time	$t_r$				64		ns
Turn-off Delay Time	$t_{d(off)}$				375		ns
Fall Time	$t_f$				72		ns
Energy Dissipation During Turn-on Time	$E_{on}$			14.5		mJ	
Energy Dissipation During Turn-off Time	$E_{off}$			10.5		mJ	
SC Data	$I_{sc}$	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$			500		A



## ● Diode-inverter

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	$I_F$		100	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	200	A
$I^2t$ -value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$	1550	A <sup>2</sup> S
		$V_R=0V, t_p=10ms, T_{vj}=150^{\circ}C$	1500	

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F=100A, T_{vj}=25^{\circ}C$		1.86	2.80	V
		$I_F=100A, T_{vj}=125^{\circ}C$		1.70		
		$I_F=100A, T_{vj}=150^{\circ}C$		1.69		
Recovered Charge	$Q_{rr}$	$I_F=100A$		8.8		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt = 3500A/\mu s$		105		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=25^{\circ}C$		3.2		mJ
Recovered Charge	$Q_{rr}$	$I_F=100A$		19.4		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt = 3500A/\mu s$		127		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=150^{\circ}C$		6.3		mJ



● **IGBT-brake-chopper**  
**Absolute Maximum Ratings**

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_C$	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	50	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	100	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	270	W

**Characteristic values**

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.7mA, T_{vj}=25^{\circ}C$	5.0	5.7	6.5	V	
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.90	2.50	V	
		$I_C=50A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.25			
		$I_C=50A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.35			
Gate Charge	$Q_G$			0.35		uC	
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$		2.60		nF	
Reverse Transfer Capacitance	$C_{res}$	$f=1MHz, T_{vj}=25^{\circ}C$		0.10		nF	
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=15\Omega$ $T_{vj}=25^{\circ}C$		168		ns	
Rise Time	$t_r$			34		ns	
Turn-off Delay Time	$t_{d(off)}$			320		ns	
Fall Time	$t_f$			78		ns	
Energy Dissipation During Turn-on Time	$E_{on}$			5.42		mJ	
Energy Dissipation During Turn-off Time	$E_{off}$			4.15		mJ	
Turn-on Delay Time	$t_{d(on)}$		$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=15\Omega$ $T_{vj}=150^{\circ}C$		179		ns
Rise Time	$t_r$				48		ns
Turn-off Delay Time	$t_{d(off)}$				506		ns
Fall Time	$t_f$				154		ns
Energy Dissipation During Turn-on Time	$E_{on}$			7.84		mJ	
Energy Dissipation During Turn-off Time	$E_{off}$			6.15		mJ	
SC Data	$I_{sc}$	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$			260		A



## ● Diode-Brake-Chopper

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	$I_F$		35	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	70	A
$I^2t$ -value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$	240	A <sup>2</sup> s
		$V_R=0V, t_p=10ms, T_{vj}=150^{\circ}C$	220	

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max	
Forward Voltage	$V_F$	$I_F=35A, T_{vj}=25^{\circ}C$		1.95	2.80	V
		$I_F=35A, T_{vj}=125^{\circ}C$		1.86		
		$I_F=35A, T_{vj}=150^{\circ}C$		1.83		
Recovered Charge	$Q_{rr}$	$I_F=35A$		4.15		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt = 1600A/\mu s$		42		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=25^{\circ}C$		1.30		mJ
Recovered Charge	$Q_{rr}$	$I_F=35A$		9.58		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600V$ $-di_F/dt = 1600A/\mu s$		52		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=150^{\circ}C$		2.86		mJ



## ● Diode-Rectifier

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}C$	80	A
Maximum RMS Current at Rectifier Output	$I_{RMSM}$	$T_C=100^{\circ}C$	120	A
Surge Forward Current	$I_{FSM}$	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	1100	A
$I^2t$ -value	$I^2t$	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	6050	A <sup>2</sup> s

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	$V_F$	$I_F=50A, T_{vj}=125^{\circ}C$		0.98		V
Reverse Current	$I_R$	$T_{vj}=125^{\circ}C, V_R=1600V$			2.0	mA

## ● NTC-Thermistor

### Characteristic values

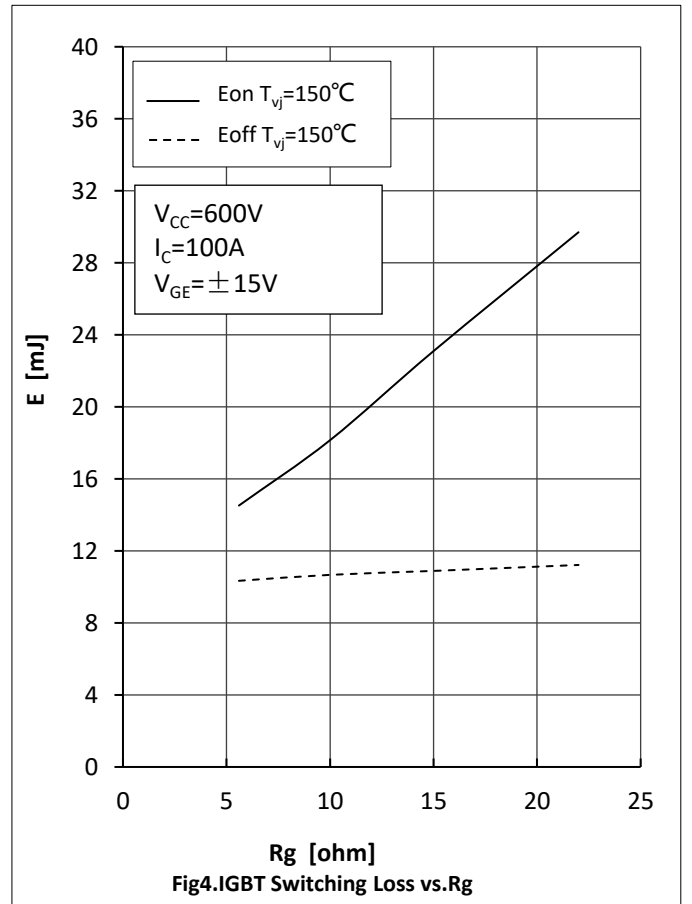
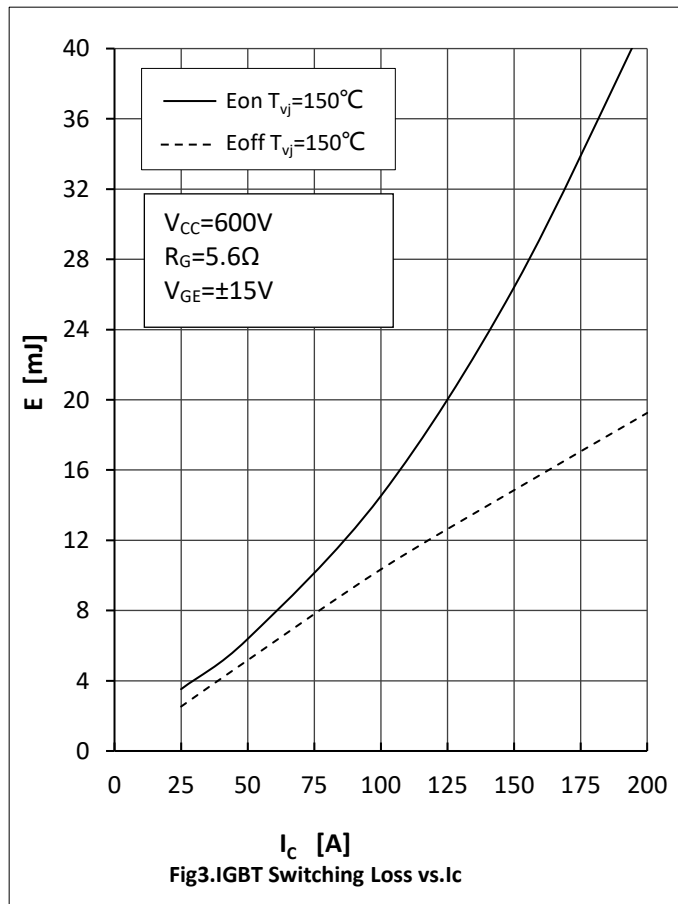
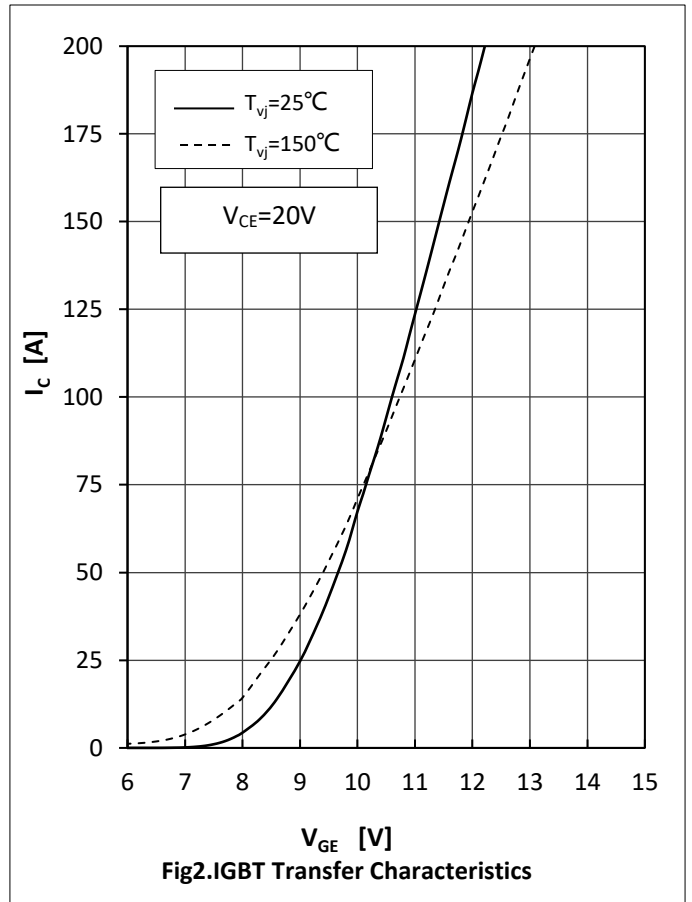
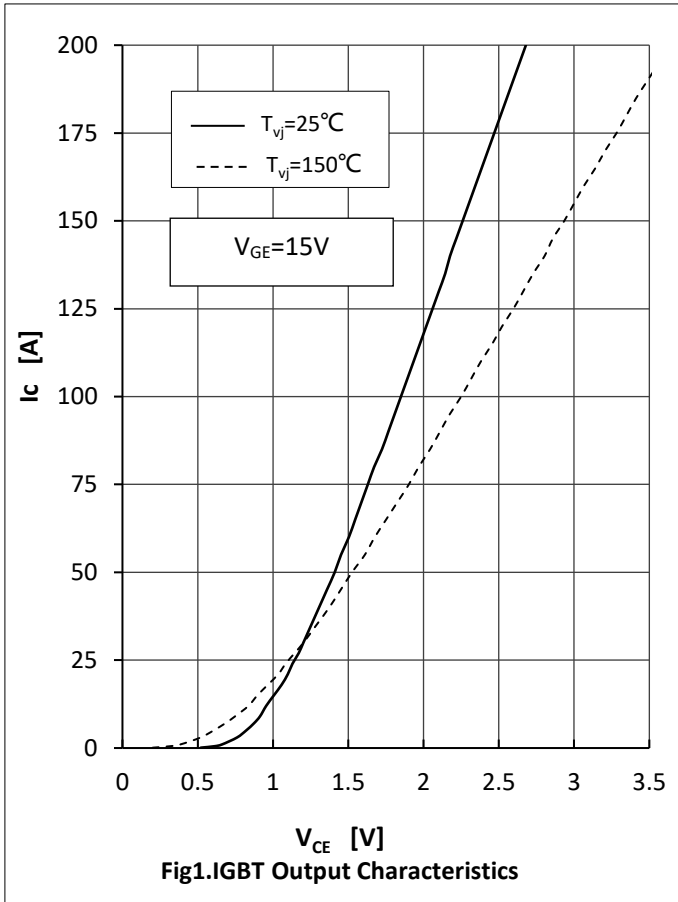
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	$R_{25}$			5.0		k $\Omega$
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	$P_{25}$				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15 K))]$		3375		K



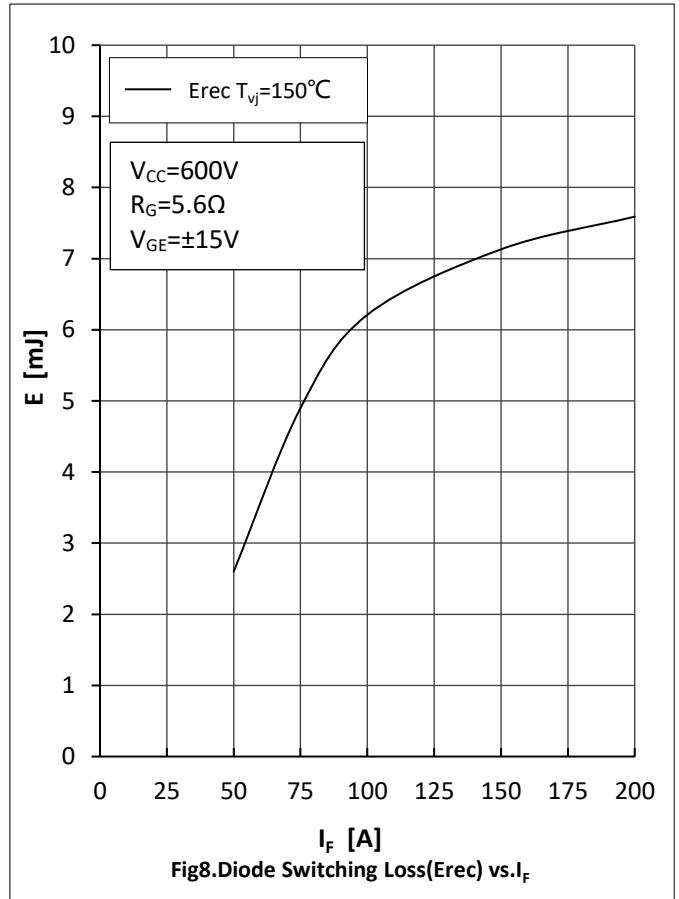
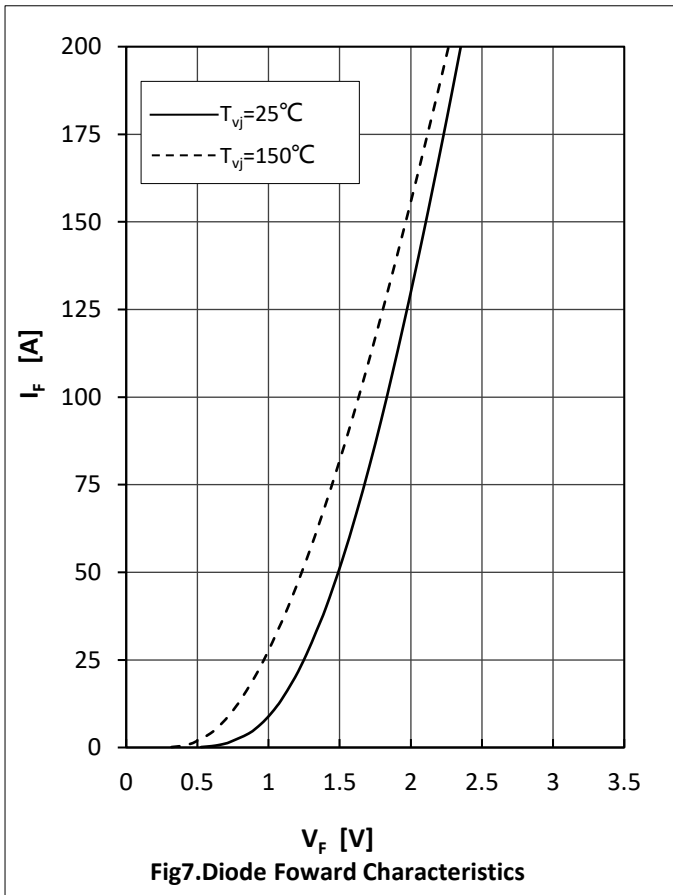
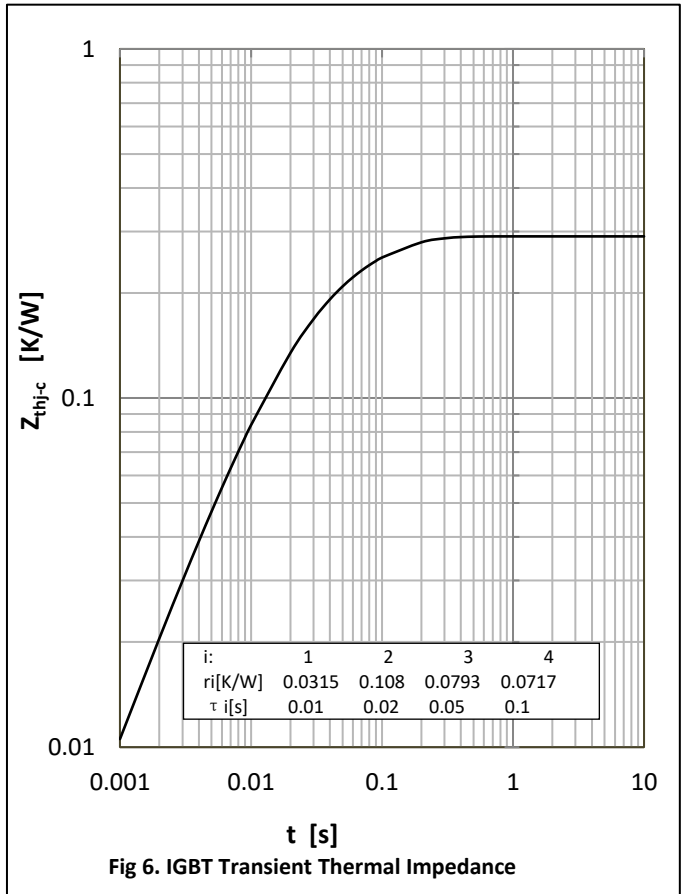
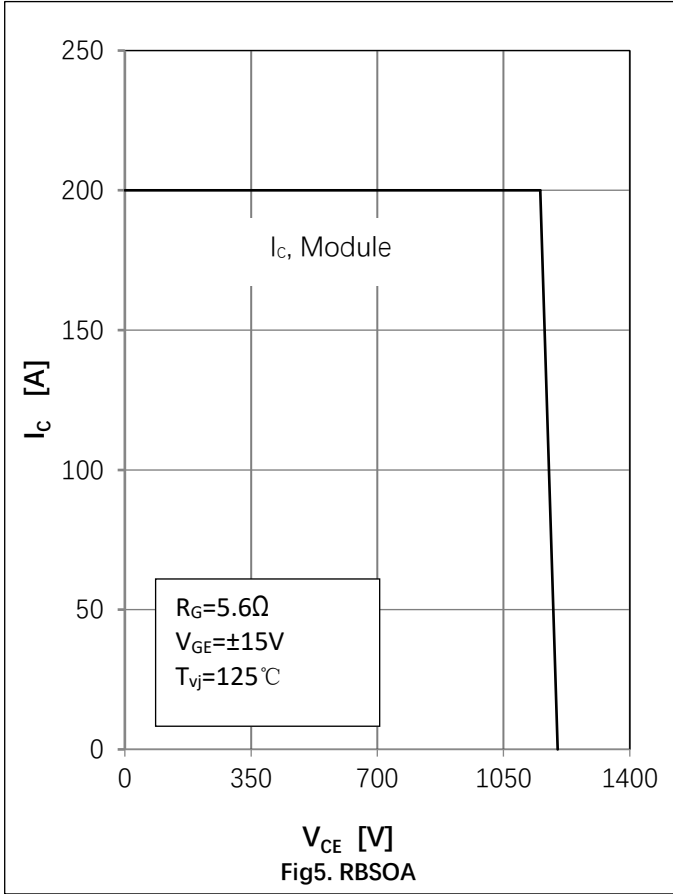
## ● Module Characteristics

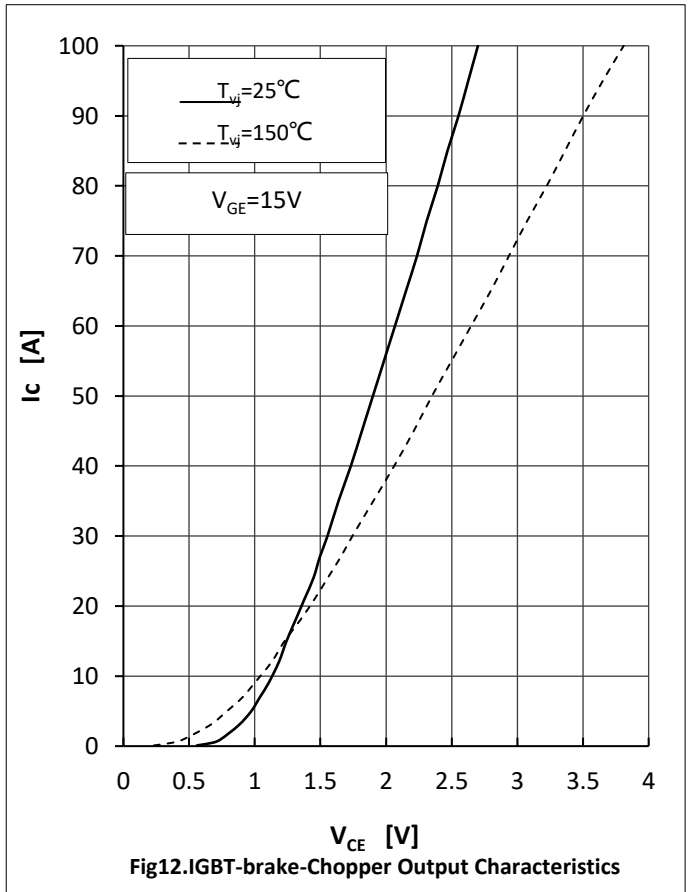
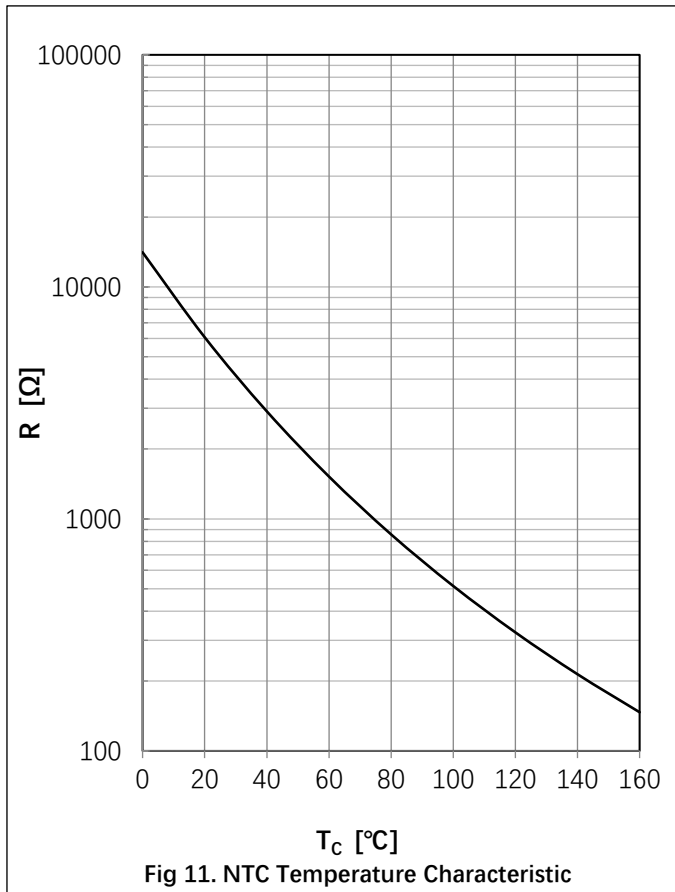
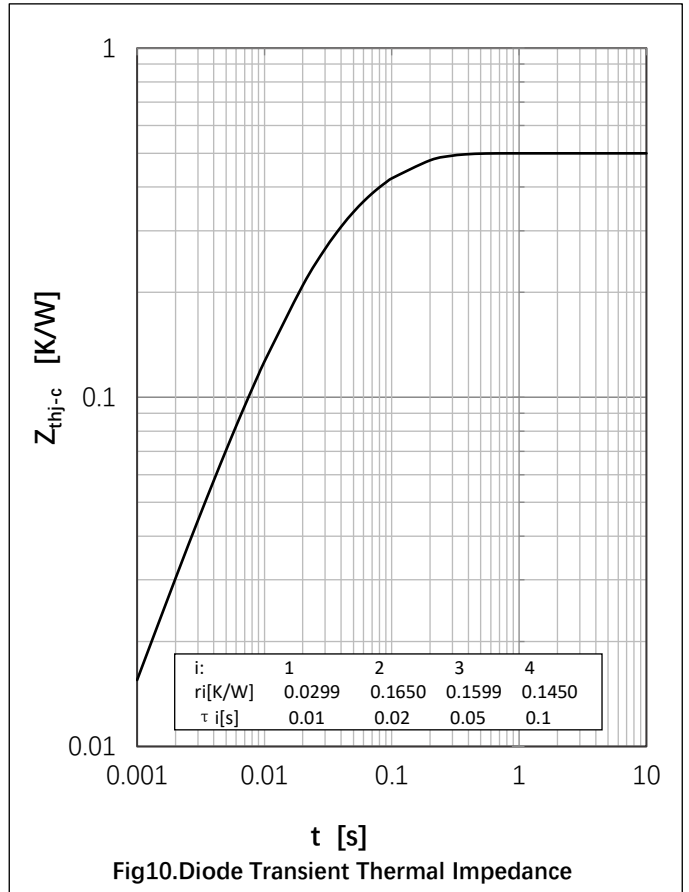
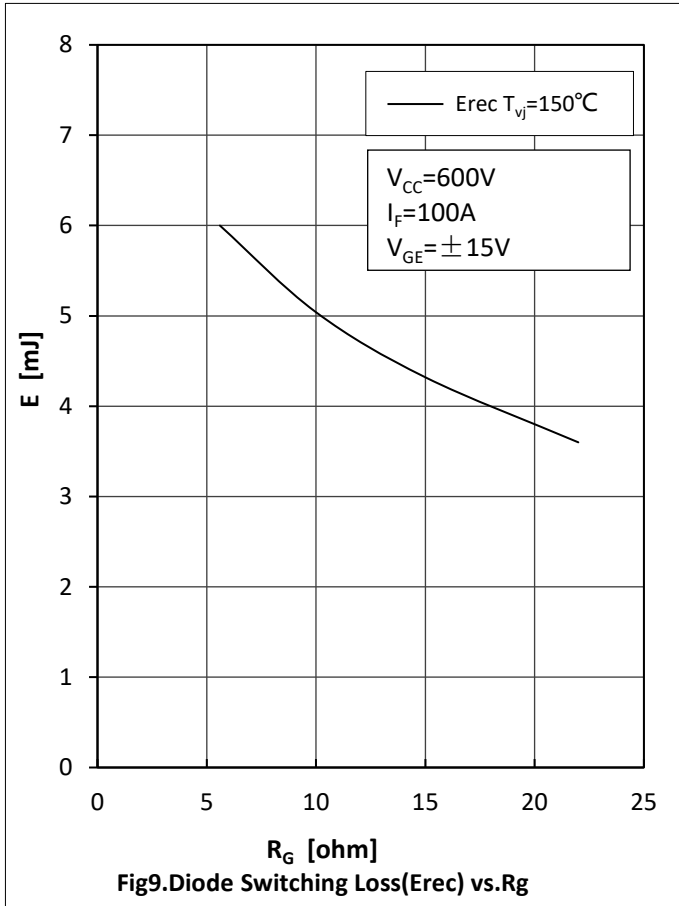
 $T_C=25^{\circ}\text{C}$  unless otherwise specified

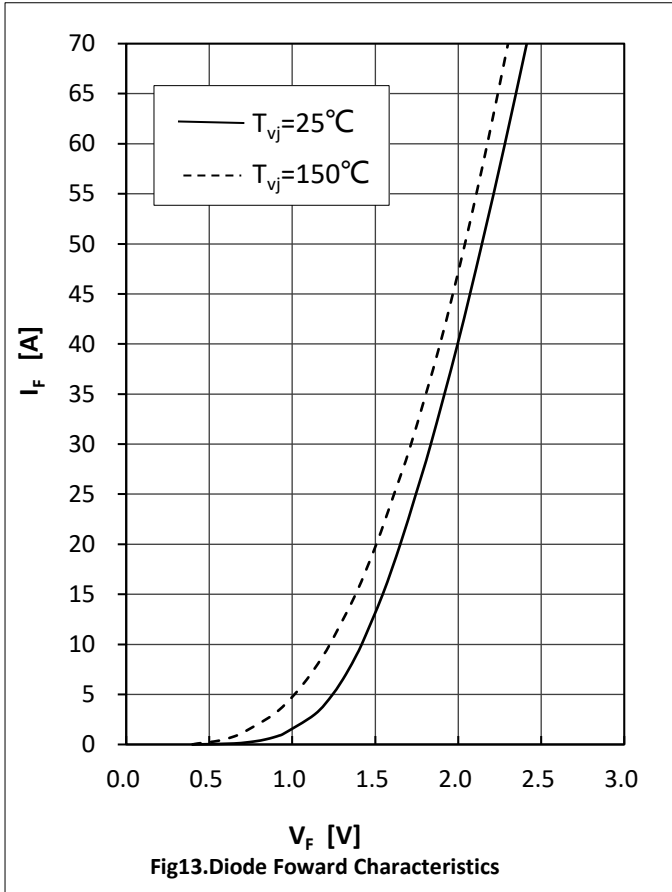
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	$V_{\text{isol}}$	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{\text{jmax}}$				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$		-40		125	$^{\circ}\text{C}$
Stray-inductance-module	$L_{\text{SCE}}$			60		nH
Comparative Tracking Index	CTI		200			
Module lead resistance, terminals-chip	$R_{\text{CC}'+\text{EE}'}$	$T_C=25^{\circ}\text{C}$ , per switch		4.0		m $\Omega$
	$R_{\text{AA}'+\text{CC}'}$			3.0		
Thermal Resistance Junction-to Case	$R_{\theta\text{JC}}$	per IGBT-inverter			0.29	K/W
		per Diode-inverter			0.50	
		per IGBT-brake-copper			0.55	
		per Diode-chopper			1.30	
		per Diode-rectifier			0.65	
Thermal Resistance Case-to Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		0.12		K/W
		per Diode-inverter		0.22		
		per IGBT-brake-copper		0.14		
		per Diode-chopper		0.56		
		per Diode-rectifier		0.19		
		per Module		0.009		
Module-to-Sink Torque	$M_s$		3.0		6.0	N·m
Weight of Module	G			300		g





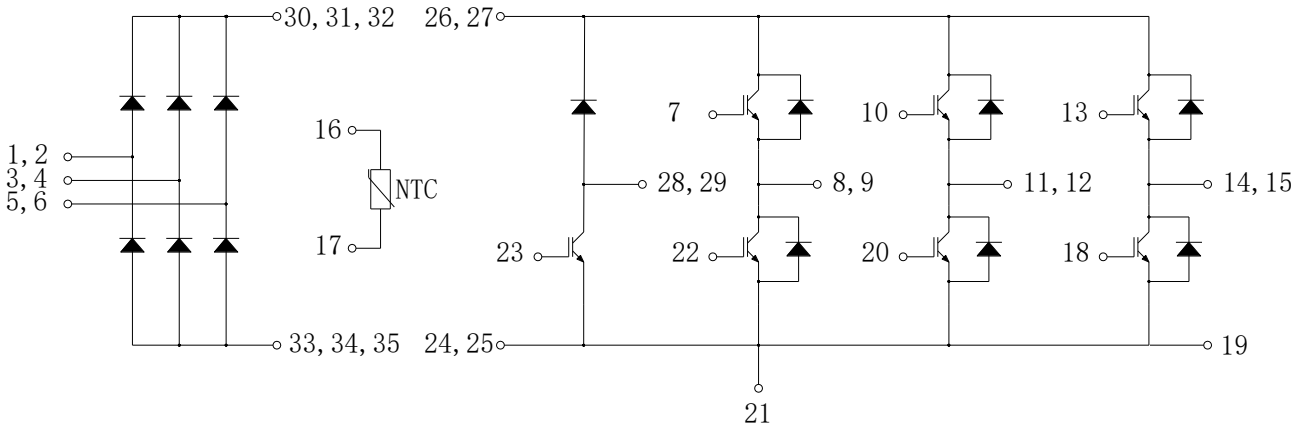




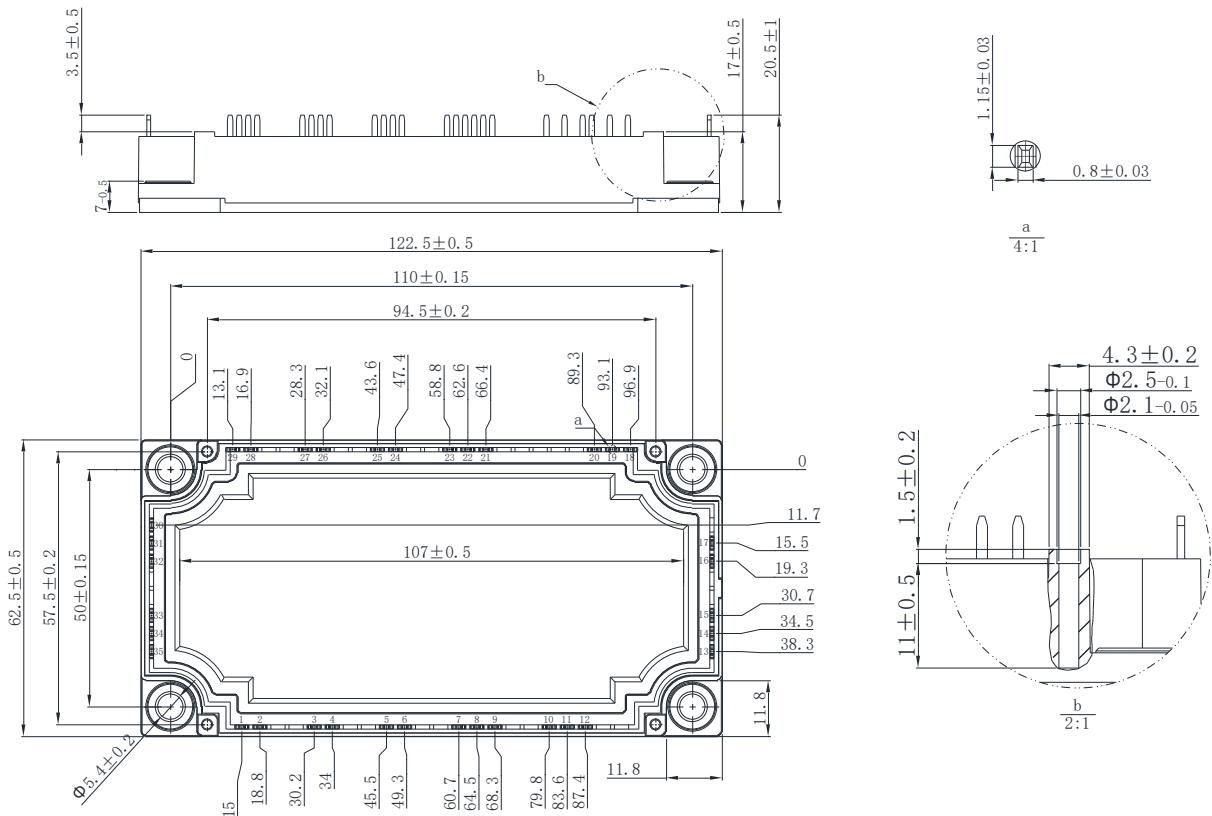




● **Circuit Diagram**



● **Package Outline Information**





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